

Program Key

Conference Topics

AC	Advanced Characterization Techniques
BG	Bulk Growth
DI	Dielectric Interfaces
EG	Epitaxial Growth
EP	Electronic and Photonic Devices, Circuits and Applications
ET	Electronic Transport and Breakdown Phenomena
HM	Heterogeneous Material Integration
KEY	Keynote Address
MD	Material and Device Processing and Fabrication Techniques
PS	Plenary Session
TM	Theory, Modeling and Simulation

Key to Session/Paper Numbers

Sessions sponsored by multiple topics are labeled with all acronyms (e.g. **AC+EM+SS**), then a number to indicate simultaneous sessions sponsored by the same topic(s) (e.g. **SS1, SS2**), then a dash followed by the first two characters of the day of the week:

Monday, Tuesday, Wednesday, Thursday, Friday, then a single letter for **Morning, Afternoon, Evening, Poster**, and finally a number indicating the starting time slot for the paper.
Example: **SS1-MoM9** (Surface Science, Monday morning, 11:00 am).

Program Overview

Room /Time	Jefferson 1 & Atrium	Jefferson 2-3
MoM		KEY1: Keynote Address AC-MoM: Characterization & Modeling I BG-MoM: Bulk & Epitaxy I
MoA		MD-MoA: Process & Devices I TM-MoA: Characterization & Modelling II
MoP	Poster Sessions	
TuM		PS1-TuM: Plenary Session I TM-TuM: Characterization & Modelling III AC-TuM: Advanced Characterization & Microscopy
TuA		EG-TuA: Bulk & Epitaxy II DI-TuA: Processes & Devices II
TuP	Poster Sessions	
WeM		PS2-WeM: Plenary Session II EP1-WeM: Process & Devices III EP2-WeM: Process and Devices IV

Monday Morning, August 8, 2022

Room Jefferson 2-3		
8:30am		Keynote Address Session KEY1 Keynote Address Moderator: Dr. Kelson Chabak, Air Force Research Laboratory
8:45am	INVITED: KEY1-2 Keynote Lecture: Ga ₂ O ₃ Device Technologies: Power Switching and High-Frequency Applications, and Beyond, Masataka Higashiwaki , Department of Physics and Electronics, Osaka Metropolitan University, Japan; T. Kamimura, S. Kumar, Z. Wang , National Institute of Information and Communications Technology, Japan; T. Kitada, J. Liang, N. Shigekawa , Department of Physics and Electronics, Osaka Metropolitan University, Japan; H. Murakami, Y. Kumagai , Department of Applied Chemistry, Tokyo University of Agriculture and Technology, Japan	
9:00am		
9:15am		
9:30am	INVITED: AC-MoM-5 Characterization of Deep Acceptors in β-Ga ₂ O ₃ by Deep Level Optical Spectroscopy, H. Ghadi, J. McGlone, E. Cornuelle , The Ohio State University; A. Senckowski , University of Massachusetts Lowell; S. Sharma, U. Singiseti , University of Buffalo; M. Wong , University of Massachusetts Lowell; A. Arehart, Steven A Ringel , The Ohio State University	Advanced Characterization Techniques Session AC-MoM Characterization & Modeling I Moderator: Kornelius Tetzner, Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik (FBH), Germany
9:45am		
10:00am	AC-MoM-7 Determination of Cation Vacancy and Al Diffusion Constants in B-(Al,Ga) ₂ O ₃ / Ga ₂ O ₃ Superlattices, H. Yang, A. Levin, B. Eisner, A. Bhattacharyya, P. Ranga, S. Krishnamoorthy, Michael Scarpulla , University of Utah	
10:15am	AC-MoM-8 Defect Characterization in Gallium Oxide and Related Materials Using Terahertz Electron Paramagnetic Resonance Ellipsometry: Fe in Ga ₂ O ₃ , Mathias Schubert , University of Nebraska, Lincoln; S. Richter , Lund University, Sweden; S. Knight, P. Kuehne , Linköping University, Sweden; M. Stokey, R. Karlacki , University of Nebraska-Lincoln; V. Stanishev , Linköping University, Sweden; Z. Galazka, K. Irmscher , Leibniz-Institut fuer Kristallzuechtung, Germany; S. Mu, C. Van de Walle , University of California at Santa Barbara; V. Ivády , MPI Physics of Complex Systems, Germany; O. Bulancea-Lindvall, I. Abrikosov , Linköping University, Sweden; V. Darakchieva , Lund University, Sweden	
10:30am	BREAK	
10:45am	INVITED: BG-MoM-10 β-Ga ₂ O ₃ Growth and Wafer Fabrication, A. Brady, G. Foundos, Chase Scott , Northrop Grumman SYNOPTICS; V. Gambin , Northrop Grumman Corporation; K. Stevens , Northrop Grumman SYNOPTICS; J. Blevins , Air Force Research Laboratory, Afghanistan	Bulk Growth Session BG-MoM Bulk & Epitaxy I Moderator: John Blevins, Air Force Research Laboratory
11:00am		
11:15am	BG-MoM-12 Increasing the Bandgap of β-Ga ₂ O ₃ via Alloying with Al ₂ O ₃ or Sc ₂ O ₃ in Czochralski-grown Crystals, Benjamin Dutton, J. Jesenovc, B. Downing, J. McCloy , Washington State University	
11:30am	BG-MoM-13 Chemi-Mechanical Polishing and Subsurface Damage Characterization of 2-inch (010) Semi-Insulating β-Ga ₂ O ₃ Substrates, David Snyder , Penn State Applied Research Laboratory	
11:45am	BG-MoM-14 Ge-Delta Doped β-Ga ₂ O ₃ Grown Via Plasma Assisted Molecular Beam Epitaxy, Thaddeus Asel , Air Force Research Laboratory, Materials and Manufacturing Directorate, USA; E. Steinbrunner , Wright State University, Department of Electrical Engineering; J. Hendrick , Air Force Institute of Technology, Department of Engineering Physics; A. Neal, S. Mou , Air Force Research Laboratory, Materials and Manufacturing Directorate, USA	
12:00pm	BG-MoM-15 High Purity n-type β-Ga ₂ O ₃ Films with 10 ¹³ cm ⁻³ Residual Acceptor Concentration by MOCVD, Andrei Osinsky, F. Alema , Agnitron Technology	

Monday Afternoon, August 8, 2022

Room Jefferson 2-3		
1:45pm	INVITED: MD-MoA-1 High Aspect Ratio Ga ₂ O ₃ -based Homo and H0eterostructures by Plasma-free Metal-assisted Chemical Etching, <i>Xiuling Li</i> , University of Texas at Austin; <i>H. Huang, C. Chan, J. Michaels</i> , University of Illinois, Urbana-Champaign	Material and Device Processing and Fabrication Techniques Session MD-MoA Process & Devices I Moderator: Man-Hoi Wong , University of Massachusetts Lowell
2:00pm		
2:15pm	MD-MoA-3 Blocking Behavior of N and Fe Ion Implanted β -Ga ₂ O ₃ , <i>Bennett Cromer</i> , Cornell University; <i>W. Li</i> , University of California at Berkeley; <i>K. Smith</i> , Cornell University; <i>K. Gann</i> , Cornell University, Iceland; <i>K. Nomoto</i> , Cornell University; <i>N. Hendriks</i> , University of California at Santa Barbara; <i>A. Green, K. Chabak</i> , Air Force Research Laboratory; <i>M. Thompson, D. Jena, G. Xing</i> , Cornell University	
2:30pm	MD-MoA-4 Evolution and Recovery of Ion Implantation-Induced Damage Zone in β -Ga ₂ O ₃ , <i>Elaf Anber, D. Foley, J. Nathaniel</i> , Johns Hopkins University; <i>A. Lang</i> , American Society for Engineering Education; <i>J. Hart</i> , Johns Hopkins University; <i>M. Tadjer, K. Hobart</i> , US Naval Research Laboratory; <i>S. Pearton</i> , University of Florida, Gainesville; <i>M. Taheri</i> , Johns Hopkins University	
2:45pm	MD-MoA-5 Heterogeneous Integration of Single-Crystal β -Ga ₂ O ₃ and N-Polar GaN Substrates With ZnO Interlayer Deposited by Atomic Layer Deposition, <i>Zhe (Ashley) Jian</i> , University of Michigan, Ann Arbor; <i>C. Clymore</i> , University of California, Santa Barbara; <i>D. Agapiou</i> , University of Michigan, Ann Arbor; <i>U. Mishra</i> , University of California, Santa Barbara; <i>E. Ahmadi</i> , University of Michigan, Ann Arbor	
3:00pm	MD-MoA-6 Structural Transformation of β -Ga ₂ O ₃ through Si-implantation, <i>Snorre Braathen Kjeldby, A. Azarov, P. Nguyen</i> , Centre for Materials Science and Nanotechnology, University of Oslo, Norway; <i>V. Venkatachalapathy</i> , Centre for Materials Science and Nanotechnology, University of Oslo and Department of Materials Science, National Research Nuclear University, "MEPhI", Norway; <i>R. Mikšová</i> , Nuclear Physics Institute of the Czech Academy of Sciences, Czechia; <i>A. Macková</i> , Nuclear Physics Institute of the Czech Academy of Sciences and Department of Physics, Faculty of Science, J.E. Purkyně University, Czechia; <i>J. García-Fernández, A. Kuznetsov, Ø. Prytz, L. Vines</i> , Centre for Materials Science and Nanotechnology, University of Oslo, Norway	
3:15pm	MD-MoA-7 Electrical Characteristics of <i>in Situ</i> Mg-Doped Ga ₂ O ₃ Current-Blocking Layer for Vertical Devices, <i>Sudipto Saha</i> , University at Buffalo-SUNY; <i>L. Meng, A. Bhuiyan, Z. Feng, H. Zhao</i> , Ohio State University; <i>U. Singiseti</i> , University at Buffalo-SUNY	
3:30pm	BREAK	
3:45pm	INVITED: TM-MoA-9 Transport, Doping, and Defects in β -Ga ₂ O ₃ , <i>Adam Neal</i> , Air Force Research Laboratory, Materials and Manufacturing Directorate, USA	Theory, Modeling and Simulation Session TM-MoA Characterization & Modelling II Moderator: Mike Thompson , Cornell University
4:00pm		
4:15pm	TM-MoA-11 Structural Changes to Beta Gallium Oxide from Ion Irradiation Damage: Model and Relation to in-Situ Experiments, <i>Alexander Petkov, D. Cherns, D. Liu</i> , University of Bristol, UK; <i>W. Chen, M. Li</i> , Argonne National Laboratory, USA; <i>J. Blevins</i> , Air Force Research Laboratory, USA; <i>V. Gambin</i> , Northrop Grumman; <i>M. Kuball</i> , University of Bristol, UK	
4:30pm	TM-MoA-12 Band Structure Across κ -(In _x Ga _{1-x}) ₂ O ₃ / κ -(Al _y Ga _{1-y}) ₂ O ₃ Thin Film Interfaces, <i>Ingvild Julie Thue Jensen, A. Thøgersen, E. Fertitta, B. Belle</i> , SINTEF Materials Physics, Norway; <i>A. Langørgen, S. Cooil, Y. Hommedal, Ø. Prytz, J. Wells, L. Vines</i> , University of Oslo, Norway; <i>H. von Wenckstern</i> , University of Leipzig, Germany	
4:45pm	TM-MoA-13 Aluminum Incorporation Striations in (-201) β -(Al _x Ga _{1-x}) ₂ O ₃ Films Grown on C-Plane and Miscut Sapphire Substrates, <i>Kenny Huynh, Y. Wang, M. Liao</i> , University of California Los Angeles; <i>P. Ranga</i> , University of Utah; <i>S. Krishnamoorthy</i> , University of California at Santa Barbara; <i>M. Goorsky</i> , University of California, Los Angeles	
5:00pm	TM-MoA-14 Plasmon-phonon Coupling in Electrostatically Gated β -Ga ₂ O ₃ Films with Mobility Exceeding 200 cm ² V ⁻¹ s ⁻¹ , <i>A. Rajapitamahuni, A. Manjeshwar</i> , University of Minnesota, USA; <i>A. Kumar, A. Datta</i> , University at Buffalo; <i>P. Ranga</i> , University of California Santa Barbara; <i>L. Thoutam</i> , SR University, Warangal, India; <i>S. Krishnamoorthy</i> , University of California Santa Barbara; <i>Uttam Singiseti</i> , University at Buffalo; <i>B. Jalan</i> , University of Minnesota, USA	

Advanced Characterization Techniques

Room Jefferson 1 & Atrium - Session AC-MoP

Advanced Characterization Techniques Poster Session

5:15pm

AC-MoP-1 Advanced Defect Characterization in β -Ga₂O₃ Without the Arrhenius Plot, *J. Li*, NCKU, Taiwan; *Adam Neal*, *S. Mou*, Air Force Research Laboratory, Materials and Manufacturing Directorate, USA; *M. Wong*, University of Massachusetts Lowell

AC-MoP-2 Infrared-Active Phonon Modes and Static Dielectric Constants of Orthorhombic LiGaO₂, *Teresa Gramer*, *M. Stokey*, *R. Korlacki*, *M. Schubert*, University of Nebraska - Lincoln

AC-MoP-3 Spectroscopic Ellipsometry Optical Analysis of Zinc Gallate at Elevated Temperatures, *Emma Williams*, University of Nebraska-Lincoln, USA; *M. Hilfiker*, *U. Kilic*, *Y. Traouli*, *N. Koeppe*, *J. Rivera*, *A. Abakar*, *M. Stokey*, *R. Korlacki*, University of Nebraska - Lincoln; *Z. Galazka*, Leibniz-Institut für Kristallzüchtung, Germany; *M. Schubert*, University of Nebraska - Lincoln

AC-MoP-4 The Electron Spin Hamiltonian for Fe³⁺ in Monoclinic β -Ga₂O₃, *S. Richter*, Lund University, Sweden; *S. Knight*, *P. Kühne*, Linköping University, Sweden; *Mathias Schubert*, University of Nebraska - Lincoln; *V. Darakchieva*, Lund University, Sweden

AC-MoP-5 Characterization of (010) β -Ga₂O₃ to Support Fabrication, Wafer Size Scaleup, and Epi Development, *David Snyder*, Penn State Applied Research Laboratory

AC-MoP-6 Photoluminescence Spectroscopy of Cr³⁺ in β -Ga₂O₃ and (Al_{0.1}Ga_{0.9})₂O₃, *Cassandra Remple*, *J. Jesenovc*, *B. Dutton*, *J. McCloy*, *M. McCluskey*, Washington State University

AC-MoP-7 Surface Relaxation and Rumpling of Sn Doped β -Ga₂O₃(010), *Nick Barrett*, CEA Saclay, France; *A. Pancotti*, Universidade Federal de Jataí, Brazil; *T. Back*, AFRL; *W. Hamouda*, *M. Laccheb*, *C. Lubin*, *A. Boucly*, CEA Saclay, France; *P. Soukiasian*, Université Paris-Saclay, France; *J. Boeckl*, *D. Dorsey*, *S. Mou*, *T. Asel*, AFRL; *G. Geneste*, CEA, France

AC-MoP-8 Probing Vacancies and Hydrogen Related Defects in β -Ga₂O₃ with Positrons and FTIR, *Corey Halverson*, *M. Weber*, *J. Jesenovc*, *B. Dutton*, *C. Remple*, *M. McCluskey*, *J. McCloy*, Washington State University

AC-MoP-9 Evolution of Anisotropy and Order of Band-to-Band Transitions, Excitons, Phonons, Static and High Frequency Dielectric Constants Including Strain Dependencies in Alpha and Beta Phase (Al_xGa_{1-x})₂O₃, *Megan Stokey*, University of Nebraska-Lincoln; *R. Korlacki*, *M. Hilfiker*, *T. Gramer*, University of Nebraska - Lincoln; *J. Knudtson*, University of Nebraska-Lincoln; *S. Richter*, Lund University, Sweden; *S. Knight*, Linköping University, Sweden; *A. Mock*, Weber State University; *A. Mauze*, *Y. Zhang*, *J. Speck*, University of California Santa Barbara; *R. Jinno*, *Y. Cho*, *H. Xing*, *D. Jena*, Cornell University; *Y. Oshima*, National Institute for Materials Science, Japan; *E. Ahmadi*, University of Michigan; *V. Darakchieva*, Lund University, Sweden; *M. Schubert*, University of Nebraska - Lincoln

AC-MoP-10 Photoluminescence Mapping of Gallium Oxide and Aluminum Gallium Oxide Epitaxial Films, *Jacqueline Cooke*, *P. Ranga*, University of Utah; *J. Jesenovc*, *J. McCloy*, Washington State University; *S. Krishnamoorthy*, University of California at Santa Barbara; *M. Scarpulla*, *B. Sensale-Rodriguez*, University of Utah

AC-MoP-12 Non-Destructive Characterization of Annealed Si-Implanted Thin Film β -Ga₂O₃, *Aine Connolly*, *K. Gann*, Cornell University; *S. Tetlak*, Air Force Research Laboratory; *V. Protasenko*, Cornell University; *M. Slocum*, *S. Mou*, Air Force Research Laboratory; *M. Thompson*, Cornell University

Dielectric Interfaces

Room Jefferson 1 & Atrium - Session DI-MoP

Dielectric Interfaces Poster Session

5:15pm

DI-MoP-1 Band Offsets of MOCVD Grown β -(Al_{0.21}Ga_{0.79})₂O₃/ β -Ga₂O₃ (010) Heterojunctions, *T. Morgan*, *J. Rudie*, *M. Zamani-Alavijeh*, *A. Kuchuk*, University of Arkansas; *N. Orishchin*, *F. Alema*, Agnitron Technology Incorporated; *A. Osinsky*, Agnitron Technology Incorporated, United States Minor Outlying Islands (the); *R. Sleezer*, Minnesota State University at Mankato; *G. Salamo*, University of Arkansas, United States Minor Outlying Islands (the); *Morgan Ware*, University of Arkansas

DI-MoP-2 Optimization of MOCVD Grown In-situ Dielectrics for β -Ga₂O₃, *G. Wang*, University of Wisconsin - Madison; *F. Alema*, Agnitron Technology Inc.; *J. Chen*, University of Wisconsin - Madison; *A. Osinsky*, Agnitron Technology Inc.; *C. Gupta*, University of Wisconsin-Madison; *Shubhra Pasayat*, University of Wisconsin - Madison

Electronic and Photonic Devices, Circuits and Applications

Room Jefferson 1 & Atrium - Session EP-MoP

Electronic and Photonic Devices, Circuits and Applications

Poster Session

5:15pm

EP-MoP-2 Gate Effects of Channel and Sheet Resistance in β -Ga₂O₃ Field-Effect Transistors using the TLM Method, *Ory Maimon*, Department of Electrical Engineering, George Mason University; *N. Moser*, Air Force Research Laboratory, Sensors Directorate; *K. Liddy*, *A. Green*, *K. Chabak*, Air Force Research Laboratory, Sensors Directorate, USA; *C. Richter*, *K. Cheung*, *S. Pookpanratana*, Nanoscale Device and Characterization Division, National Institute of Standards and Technology; *Q. Li*, Department of Electrical Engineering, George Mason University

EP-MoP-3 Lateral β -Ga₂O₃ Schottky Barrier Diodes With Interdigitated Contacts, *Jeremiah Williams*, Air Force Research Laboratory, Sensors Directorate; *A. Arias-Purdue*, Teledyne; *K. Liddy*, *A. Green*, Air Force Research Laboratory, Sensors Directorate; *D. Dryden*, *N. Sepelak*, KBR; *K. Singh*, Air Force Research Laboratory, Sensors Directorate; *F. Alema*, *A. Osinsky*, Agnitron Technology; *A. Islam*, *N. Moser*, *K. Chabak*, Air Force Research Laboratory, Sensors Directorate

EP-MoP-4 Optimized Annealing for Activation of Implanted Si in β -Ga₂O₃, *Katie Gann*, *J. McCandless*, Cornell University; *T. Asel*, *S. Tetlak*, Air Force Research Laboratory; *D. Jena*, *M. Thompson*, Cornell University

Electronic Transport and Breakdown Phenomena

Room Jefferson 1 & Atrium - Session ET-MoP

Electronic Transport and Breakdown Phenomena Poster

Session

5:15pm

ET-MoP-2 Electric Field Mapping in β -Ga₂O₃ by Photocurrent Spectroscopy, *Darpan Verma*, *M. Adnan*, *S. Dhara*, Ohio State University; *C. Sturm*, Universität Leipzig, Germany; *S. Rajan*, *R. Myers*, Ohio State University

ET-MoP-3 Activation of Si, Ge, and Sn Donors in High-Resistivity Halide Vapor Phase Epitaxial β -Ga₂O₃:N, *Joseph Spencer*, Naval Research Laboratory/Virginia Tech CPES; *M. Tadjer*, *A. Jacobs*, *M. Mastro*, *J. Gallagher*, *J. Freitas, Jr*, Naval Research Laboratory; *T. Tu*, *A. Kuramata*, *K. Sasaki*, Novel Crystal, Japan; *Y. Zhang*, Virginia Tech (CPES); *T. Anderson*, *K. Hobart*, Naval Research Laboratory

Heterogeneous Material Integration

Room Jefferson 1 & Atrium - Session HM-MoP

Heterogeneous Material Integration Poster Session

5:15pm

HM-MoP-1 Structural and Thermal Transport Analysis of Wafer Bonded β -Ga₂O₃ |4H-SiC, *Michael Liao*, *K. Huynh*, *Y. Wang*, UCLA; *Z. Cheng*, UIUC; *J. Shi*, GaTech; *F. Mu*, IMECAS, China; *T. You*, *W. Xu*, *X. Ou*, ShanghaiTech, China; *T. Suga*, Meisei University, Japan; *S. Graham*, GaTech; *M. Goorsky*, UCLA

HM-MoP-2 Advances in Plasma-Enhanced Atomic Layer Deposited (PEALD) Ga₂O₃ Films, *Virginia Wheeler*, *A. Lang*, *N. Nepal*, *E. Jin*, *D. Katzer*, *V. Gokhale*, *B. Downey*, *D. Meyer*, US Naval Research Laboratory

HM-MoP-3 Grafted Si/Ga₂O₃ pn Diodes, *H. Jang*, *D. Kim*, University of Wisconsin - Madison; *J. Gong*, University of Wisconsin at Madison; *F. Alema*, *A. Osinsky*, Agnitron Technology Inc.; *K. Chabak*, Air Force Research Laboratory; *G. Jessen*, BAE Systems; *G. Vincent*, Northrup Grumman; *S. Pasayat*, *C. Gupta*, University of Wisconsin - Madison; *Zhenqiang Ma*, 1415 Engineering Drive

Tuesday Morning, August 9, 2022

Room Jefferson 2-3		
8:30am		Plenary Session Session PS1-TuM Plenary Session I Moderator: Dr. Kelson Chabak , Air Force Research Laboratory
8:45am	INVITED: PS1-TuM-2 Plenary Lecture: Gallium Oxide Electronics - Device Engineering Toward Ultimate Material Limits, Siddharth Rajan , The Ohio State University	
9:00am		
9:15am	INVITED: TM-TuM-4 First-Principles Modeling of Ga ₂ O ₃ , Hartwin Peelaers , University of Kansas	Theory, Modeling and Simulation Session TM-TuM Characterization & Modelling III Moderator: Michael Scarpulla , University of Utah
9:30am		
9:45am	TM-TuM-6 Theory of Acceptor-Donor Complexes in Ga ₂ O ₃ , I. Chatratin , F. Sabino , University of Delaware; P. Reunchan , Kasetsart University, Thailand; Anderson Janotti , University of Delaware	
10:00am	TM-TuM-7 Donor Doping of Monoclinic and Corundum (Al _x Ga _{1-x}) ₂ O ₃ , Darshana Wickramaratne , US Naval Research Laboratory; J. Varley , Lawrence Livermore National Laboratory; J. Lyons , US Naval Research Laboratory	
10:15am	TM-TuM-8 The Co-Design, Fabrication, and Characterization of a Ga ₂ O ₃ -on-SiC MOSFET, Yiwen Song , Pennsylvania State University; A. Bhattacharyya , University of Utah; A. Karim , D. Shoemaker , Pennsylvania State University; H. Huang , Ohio State University; C. McGray , Modern Microsystems, Inc.; J. Leach , Kyma Technologies, Inc.; J. Hwang , Ohio State University; S. Krishnamoorthy , University of California at Santa Barbara; S. Choi , Pennsylvania State University	
10:30am	BREAK	
10:45am	INVITED: AC-TuM-10 Defects in Gallium Oxide – How We “See” and Understand Them, Jinwoo Hwang , The Ohio State University	
11:00am		Advanced Characterization Techniques Session AC-TuM Advanced Characterization & Microscopy Moderator: Ginger Wheeler , Naval Research Laboratory
11:15am	AC-TuM-12 Atomic-Scale Investigation of Point and Extended Defects in Ion Implanted β-Ga ₂ O ₃ , Hsien-Lien Huang , C. Chae , The Ohio State University; A. Senckowski , M. Wong , Penn State University; J. Hwang , The Ohio State University	
11:30am	AC-TuM-13 Microscopic and Spectroscopic Analysis of (100), (-201) and (010) (Al _x Ga _{1-x}) ₂ O ₃ Films Using Atom Probe Tomography, J. Sarker , University at Buffalo-SUNY; A. Bhuiyan , Z. Feng , L. Meng , H. Zhao , The Ohio State University; Baishakhi Mazumder , University at Buffalo-SUNY	
11:45am	AC-TuM-14 Phase and Microstructure Evolution of κ-Ga ₂ O ₃ Thin Films Grown by MOCVD, Jingyu Tang , K. Jiang , Carnegie Mellon University, China; M. Cabral , A. Park , Carnegie Mellon University; L. Gu , Carnegie Mellon University, China; R. Davis , L. Porter , Carnegie Mellon University	
12:00pm	AC-TuM-15 Investigation of Extended Defects in Ga ₂ O ₃ Substrates and Epitaxial Layers using X-ray Topography, Nadeemullah A. Mahadik , M. Tadjer , T. Anderson , K. Hobart , Naval Research Laboratory, USA; K. Sasaki , A. Kuramata , Novel Crystal Technology, Japan	

Tuesday Afternoon, August 9, 2022

Room Jefferson 2-3			
1:45pm	INVITED: EG-TuA-1 Progress in Beta-Gallium Oxide Materials and Properties, <i>James Speck</i> , University of California Santa Barbara	Epitaxial Growth Session EG-TuA Bulk & Epitaxy II Moderator: Xiuling Li, University of Texas Austin	
2:00pm			
2:15pm	EG-TuA-3 (110) β-Ga₂O₃ Epitaxial Films Grown by Plasma-Assisted Molecular Beam Epitaxy, <i>Takeki Itoh, A. Mauze, Y. Zhang, J. Speck</i> , University of California at Santa Barbara		
2:30pm	EG-TuA-4 Si-doped β -Ga ₂ O ₃ Films Grown at 1 μ m/hr by Suboxide MBE, <i>Kathy Azizie, P. Vogt, F. Hensling, D. Schlom, J. McCandless, H. Xing, D. Jena</i> , Cornell University; <i>D. Dryden, A. Neal, S. Mou, T. Asef, A. Islam, A. Green, K. Chabak</i> , Air Force Research Laboratory		
2:45pm	INVITED: EG-TuA-5 MOCVD Growth of Ga ₂ O ₃ and (Al _x Ga _{1-x}) ₂ O ₃ , <i>Hongping Zhao</i> , The Ohio State University		
3:00pm			
3:15pm			
3:30pm	BREAK		
3:45pm	DI-TuA-9 Dielectric Integration on (010) β -Ga ₂ O ₃ : Al ₂ O ₃ , SiO ₂ Interfaces and their Thermal Stability, <i>Ahmad Islam</i> , Air Force Research Laboratory; <i>A. Miesle</i> , University of Dayton; <i>M. Dietz</i> , Wright State University; <i>K. Leedy, S. Ganguli</i> , Air Force Research Laboratory; <i>G. Subramanyam</i> , University of Dayton; <i>W. Wang</i> , Wright State University; <i>N. Sepelak, D. Dryden</i> , KBR, Inc.; <i>T. Asef, A. Neal, S. Mou, S. Tetlak, K. Liddy, A. Green, K. Chabak</i> , Air Force Research Laboratory		Dielectric Interfaces Session DI-TuA Processes & Devices II Moderator: Hongping Zhao, Ohio State University
4:00pm	DI-TuA-10 Deep Etch Field-Terminated β -Ga ₂ O ₃ Schottky Barrier Diodes With 4.2 MV/cm Parallel Plate Field Strength, <i>Sushovan Dhara, N. Kalarickala, A. Dheenan, C. Jaishi, S. Rajan</i> , The Ohio State University		
4:15pm	DI-TuA-11 Demonstration of Low Thermal Resistance in Ga ₂ O ₃ Schottky Diodes by Junction-Side-Cooled Packaging, <i>Boyan Wang, M. Xiao, J. Knall, Y. Qin</i> , Virginia Polytechnic Institute and State University; <i>J. Spencer, M. Tadjer</i> , U.S. Naval Research Laboratory; <i>C. Buttay</i> , Univ Lyon, CNRS, INSA Lyon, Université Claude Bernard Lyon 1, Ecole Centrale de Lyon, Ampère, France; <i>K. Sasaki</i> , Novel Crystal Technology, Japan; <i>G. Lu, C. DiMarino, Y. Zhang</i> , Virginia Polytechnic Institute and State University		
4:30pm	DI-TuA-12 High Temperature In-situ MOCVD-grown Al ₂ O ₃ Dielectric on (010) β -Ga ₂ O ₃ with 10 MV/cm Breakdown Field, <i>Saurav Roy</i> , University of California Santa Barbara; <i>A. Bhattacharyya</i> , University of Utah; <i>C. Peterson, S. Krishnamoorthy</i> , University of California Santa Barbara		
4:45pm	DI-TuA-13 Metal Oxide (PtOX) Schottky Contact with High-k Dielectric Field Plate for Improved Field Management in Vertical β -Ga ₂ O ₃ Devices, <i>Esmat Farzana</i> , University of California Santa Barbara; <i>A. Bhattacharyya</i> , The University of Utah; <i>T. Itoh, S. Krishnamoorthy, J. Speck</i> , University of California Santa Barbara		
5:00pm	DI-TuA-14 Field Plated β -Ga ₂ O ₃ Mis Diodes with High-k TiO ₂ Interlayer for Increased Breakdown and Reduced Leakage Current, <i>Nolan Hendricks</i> , Air Force Research Laboratory; UC Santa Barbara; <i>A. Green, A. Islam, K. Leedy, K. Liddy, J. Williams</i> , Air Force Research Lab; <i>E. Farzana, J. Speck</i> , UC Santa Barbara; <i>K. Chabak</i> , Air Force Research Lab		

Epitaxial Growth

Room Jefferson 1 & Atrium - Session EG-TuP

Epitaxial Growth Poster Session

5:15pm

EG-TuP-1 α -phase Gallium Oxide Thin Films Stabilized on a-, r- and m-plane Sapphire Substrates via Reactive Magnetron Sputtering and Pulsed Laser Deposition, *Edgars Butanovs*, Institute of Solid State Physics University of Latvia

EG-TuP-2 Epitaxial Growth of $(Al_xGa_{1-x})_2O_3$ by Suboxide MBE, *Jacob Steele, K. Azizie, J. McCandless*, Cornell University; *T. Asef*, Air Force Research Lab; *H. Xing, D. Jena, D. Schlom*, Cornell University

EG-TuP-5 Free Carrier Control in Homoepitaxial β -Ga₂O₃ Thin Films by Tin Impurity Doping, *Neeraj Nepal, B. Downey, V. Wheeler, D. Katzer, E. Jin, M. Hardy, V. Gokhale, T. Growden*, US Naval Research Laboratory; *K. Chabak*, Air Force Research Laboratory; *D. Meyer*, US Naval Research Laboratory

EG-TuP-6 MBE Growth of Doped and Insulating Homoepitaxial β -Ga₂O₃, *Jon McCandless, V. Protasenko, B. Morell*, Cornell University; *E. Steinbrunner, A. Neal*, Air Force Research Laboratory, Materials and Manufacturing Directorate, USA; *Y. Cho, N. Tanen, H. Xing, D. Jena*, Cornell University

EG-TuP-7 High Conductivity Homoepitaxial β -Ga₂O₃ Regrowth Layers by Pulsed Laser Deposition, *Hyung Min Jeon*, KBR; *K. Leedy*, Air Force Research Laboratory

EG-TuP-9 Highly conductive β -Ga₂O₃ and $(Al_xGa_{1-x})_2O_3$ epitaxial films by MOCVD, *Fikadu Alema*, Agnitron Technology; *T. Itoh, J. Speck*, Materials Department, University of California, Santa Barbara; *A. Osinsky*, Agnitron Technology

Material and Device Processing and Fabrication Techniques

Room Jefferson 1 & Atrium - Session MD-TuP

Material and Device Processing and Fabrication Techniques

Poster Session

5:15pm

MD-TuP-1 Record Low Specific Resistance Ohmic Contacts to Highly Doped MOVPE-Grown β -Ga₂O₃ and β - $(Al_xGa_{1-x})_2O_3$ Epitaxial Films, *Carl Peterson*, University of California Santa Barbara; *F. Alema*, Agnitron Technology; *S. Roy*, University of California Santa Barbara; *A. Bhattacharyya*, University of Utah; *A. Osinsky*, Agnitron Technology; *S. Krishnamoorthy*, University of California Santa Barbara

MD-TuP-3 MOCVD β -Ga₂O₃ Gate-recessed MESFET, *Hannah Masten, J. Lundh, J. Spencer*, US Naval Research Laboratory; *F. Alema, A. Osinsky*, Agnitron Technology; *A. Jacobs, K. Hobart, M. Tadjer*, US Naval Research Laboratory

MD-TuP-4 Subsurface Damage Analysis of Chemical Mechanical Polished (010) β -Ga₂O₃ Substrates, *Michael Liao, K. Huynh, L. Matto, D. Luccioni, M. Goorsky*, UCLA

MD-TuP-5 Diffusion of Zn in β -Ga₂O₃, *Ylva Knausgård Hommedal, Y. Frodason, L. Vines, K. Johansen*, Centre for Materials Science and Nanotechnology/Dep. of Physics, University of Oslo, Norway

MD-TuP-6 Initial Nucleation of Metastable γ -Ga₂O₃ During sub-Millisecond Thermal Anneals of Amorphous Ga₂O₃, *Katie Gann, C. Chang, M. Chang, D. Sutherland, A. Connolly, D. Muller, R. van Dover, M. Thompson*, Cornell University

MD-TuP-7 Heavily Doped β -Ga₂O₃ Deposited by Magnetron Sputtering, *Adetayo Adedeji*, Elizabeth City State University; *J. Lawson, C. Ebbing*, University of Dayton Research Institute; *J. Merrett*, Air Force Research Laboratory

MD-TuP-8 Point Defect Distributions in Ultrafast Laser Induced Periodic Surface Structures on β -Ga₂O₃, *D. Ramdin, E. DeAngelis, M. Noor, M. Haseman, E. Chowdhury, Leonard Brillson*, Ohio State University

Theory, Modeling and Simulation

Room Jefferson 1 & Atrium - Session TM-TuP

Theory, Modeling and Simulation Poster Session

5:15pm

TM-TuP-1 Simulation Study of Single Event Effects in Ga₂O₃ Schottky Diodes, *Animesh Datta, U. Singiseti*, University at Buffalo

TM-TuP-2 Anisotropic Photoresponsivity and Deviation from Beer-Lambert Law in Beta Gallium Oxide, *Md Mohsinur Rahman Adnan, D. Verma, S. Dhara*, The Ohio State University; *C. Sturm*, Universitat Leipzig, Germany; *S. Rajan, R. Myers*, The Ohio State University

TM-TuP-4 Self-Trapped Holes and Polaronic Acceptors in Ultrawide Bandgap Oxides, *John Lyons*, US Naval Research Laboratory

TM-TuP-5 Modeling for a High-Temperature Ultra-Wide Bandgap Gallium Oxide Power Module, *Benjamin Albano*, Virginia Tech Center for Power Electronics Systems; *B. Wang, C. DiMarino, Y. Zhang*, Virginia Tech Center for Power Electronics

TM-TuP-6 Atomic Surface Structure of Sn doped β -Ga₂O₃(010) Studied by Low-energy Electron Diffraction, *Alexandre Pancotti*, Universidade Federal de Jataí, Brazil; *J. T. Sadowski*, Center for Functional Nanomaterials, Brookhaven National Laboratory; *A. Sandre Kilian*, Universidade Federal de Jataí, Brazil; *D. Duarte dos Reis*, Universidade Federal do Mato Grosso do Sul, Brazil; *C. Lubin*, SPEC, CEA, CNRS, Université Paris-Saclay, CEA Saclay, France; *A. Boucly*, SPEC, CEA, CNRS, Université Paris-Saclay, France; *P. Soukiasian*, SPEC, CEA, CNRS, Université Paris-Saclay, CEA Saclay, France; *J. Boeckl, D. Dorsey*, Air Force Research Laboratory; *M. Shin, T. ASEL*, Air Force Research Lab; *J. Brown, N. Barrett*, SPEC, CEA, CNRS, Université Paris-Saclay, CEA Saclay, France; *T. Back*, SPEC, CEA, CNRS, Université Paris-Saclay, CEA Saclay

Wednesday Morning, August 10, 2022

Room Jefferson 2-3		
8:30am		Plenary Session Session PS2-WeM Plenary Session II Moderator: Dr. Kelson Chabak , Air Force Research Laboratory
8:45am	INVITED: PS2-WeM-2 Plenary Lecture: Fundamental Limits of Ga ₂ O ₃ Power Devices and How to Get There, Huili Grace Xing , Cornell University	
9:00am		
9:15am	EP1-WeM-4 Remarkable Improvement of Conductivity in B-Ga ₂ O ₃ by High-Temperature Si Ion Implantation, Arka Sardar , T. Isaacs-Smith, S. Dhar, Auburn University; J. Lawson, N. Merrett, Air Force Research Laboratory, USA	Electronic and Photonic Devices, Circuits and Applications Session EP1-WeM Process & Devices III Moderator: Uttam Singiseti , University of Buffalo, SUNY
9:30am	INVITED: EP1-WeM-5 Towards Lateral and Vertical Ga ₂ O ₃ Transistors for High Voltage Power Switching, Kornelius Tetzner , J. Würfl, E. Bahat-Treidel, O. Hilt, Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik (FBH), Germany; Z. Galazka, S. Bin Anooz, A. Popp, Leibniz-Institut für Kristallzüchtung (IKZ), Germany	
9:45am		
10:00am	EP1-WeM-7 Comparison of β-Ga ₂ O ₃ Mosfets With TiW and NiAu Metal Gates for High-Temperature Operation, Nicholas Sepelak , KBR, Wright State University; D. Dryden, KBR; R. Kahler, University of Texas at Dallas; J. William, Air Force Research Lab, Sensors Directorate; T. Asef, Air Force Research Laboratory, Materials and Manufacturing Directorate; H. Lee, University of Illinois at Urbana-Champaign; K. Gann, Cornell University; A. Popp, Leibniz-Institut für Kristallzüchtung, Germany; K. Liddy, Air Force Research Lab, Sensors Directorate; K. Leedy, Air Force Research Laboratory, Sensors Directorate; W. Wang, Wright State University; W. Zhu, University of Illinois at Urbana-Champaign; M. Thompson, Cornell University; S. Mou, Air Force Research Laboratory, Materials and Manufacturing Directorate, USA; K. Chabak, A. Green, Air Force Research Laboratory, Sensors Directorate; A. Islam, Air Force Research Laboratory, Sensors Directorate	
10:15am	EP1-WeM-8 High Electron Mobility Si-doped β-Ga ₂ O ₃ MESFETs, Arkka Bhattacharyya , University of Utah; S. Roy, University of California at Santa Barbara; P. Ranga, University of Utah; S. Krishnamoorthy, University of California at Santa Barbara	
10:30am	BREAK	
10:45am	EP2-WeM-10 β-Ga ₂ O ₃ Lateral FinFETs Formed by Atomic Ga Flux Etching, Ashok Dheenana , N. Kalarickal, Z. Feng, L. Meng, The Ohio State University; A. Fiedler, IKZ Berlin, Germany; C. Joishi, A. Price, J. McGlone, S. Dhara, S. Ringel, H. Zhao, S. Rajan, The Ohio State University	Electronic and Photonic Devices, Circuits and Applications Session EP2-WeM Process and Devices IV Moderator: Christina DiMarino , Virginia Tech
11:00am	EP2-WeM-11 Insights Into the Behaviour of Leakage Current in Lateral Ga ₂ O ₃ Transistors on Semi-Insulating Substrates, Z. Chen, A. Mishra, M. Smith, T. Moule, University of Bristol, UK; M. Uren, University of Bristol, UK; S. Kumar, Masataka Higashiwaki , National Institute of Information and Communications Technology, Japan; M. Kuball, University of Bristol, UK	
11:15am	EP2-WeM-12 Device Figure of Merit Performance of Scaled Gamma-Gate β-Ga ₂ O ₃ MOSFETs, Kyle Liddy , A. Islam, J. Williams, D. Walker, N. Moser, D. Dryden, N. Sepelak, K. Chabak, A. Green, AFRL	
11:30am	EP2-WeM-13 Electromigration of Native Point Defects and Breakdown in Ga ₂ O ₃ Vertical Devices, M. Haseaman, D. Ramdin, Ohio State University; W. Li, K. Nomoto, D. Jena, G. Xing, Cornell University; Leonard Brillson , Ohio State University	

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